

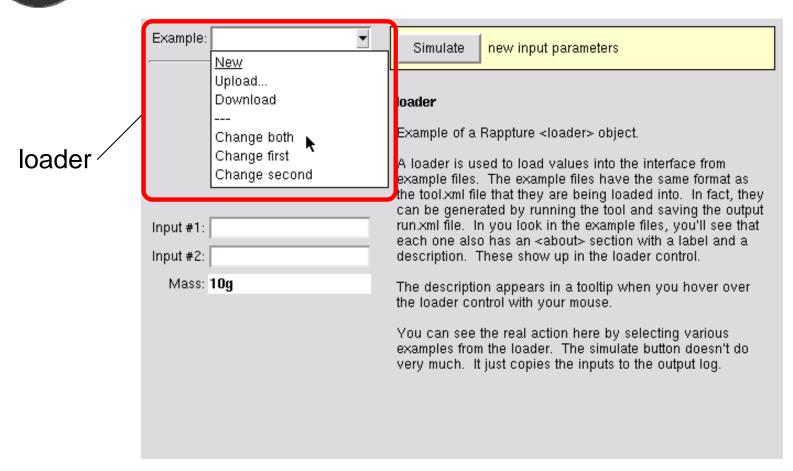
# Using the Loader

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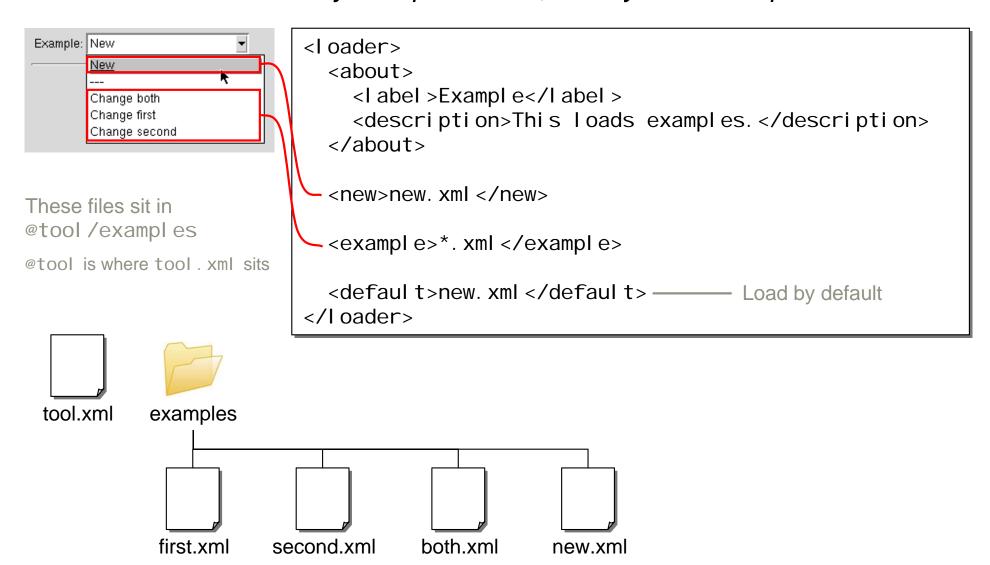
# Introducing the loader...



#### Change both Change first Change second New Input #1: first Input #1: hello Input #1: hello Input #1: (enter a value here) Input #2: second Input #2: goodbye Input #2: (enter a value here) Input #2: second Mass: 10g Mass: 10g Mass: 10g Mass: 10g



#### Put the loader definition in your input section, usually near the top:





## How do you make an example file?

```
cp tool.xml examples/both.xml vi examples/both.xml
```

```
<?xml versi on="1.0"?>
                          <run>
                          <about>
                            <label >Change both</label >
Add a description
                            <description>This example changes both inputs,
for the example
                          #1 to "first" and #2 to "second"</description>
                          </about>
                          <i nput>
                            <string id="one">
                               <current>fi rst</current>
Set a <current>
                            </string>
value for each
                            <string id="two">
element you want
                              <current>second</current>
to set
                            </string>
                          </input>
                          </run>
```



# More complex example

https://nanohub.org/tools/rtd

#### loader Device: 3-barrier device About this tool new input parameters Simulate Questions? Ambient temperature: **—— 300K** Resonant Tunneling Diodes Applied bias: - P OV leaves these alone gy levels of resonant turniening arouses produces negative unferential resistance. Study the effects of various material layers and their properties Thickness B1: 5nm on I/V characteristics. Thickness W1: 5nm Choose a structure from the list on the left. The structures are Thickness B2: 5nm composed of a stack of material layers with either pure GaAs or AlGaAs with a mole fraction x (representing the amount of Al in Thickness W2: 5nm the alloy). With x=0, the material is pure GaAs. With higher values of x, the added Al increases the band gap and the Thickness B3: 5nm effective mass, creating barriers to electronic conduction. Adjust Contact B1 W1 B2 W2 B3 Contact doping densities and material properties if you like, then push the Simulate button. Simulation results will appear here. This application is powered by: SEQUAL: Semiconductor Electrostatics by QUantum Analysis 1E19 Doping (/cm3) (v2.1)written by Michael McLennan, School of Electrical Engineering. e+18/cm3 1e+18/cm3 Purdue University, 1989. 1E18 1E17 -Doping Mole Fraction x

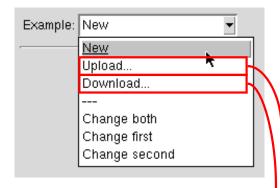
loads a <structure> element

5



# Using the loader to upload/download data

#### Add targets for upload/download forms



Prompts the user to upload directly into various controls

Most useful for <string> inputs

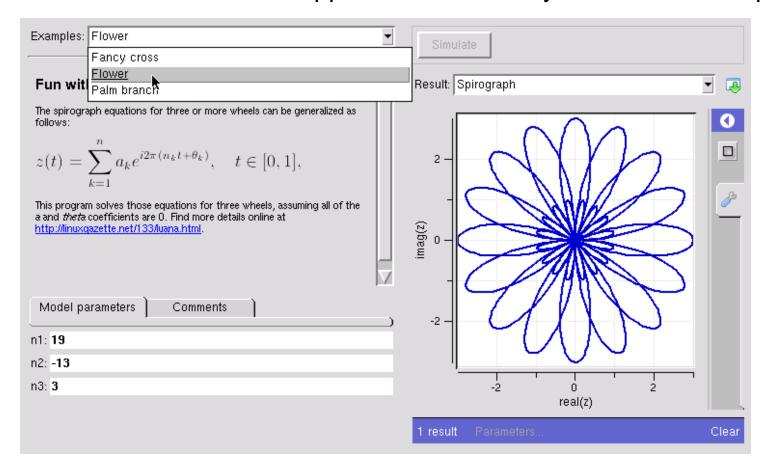
Allows the user to download input values, edit, and upload again

```
<l oader>
  <about>
    <l abel >Exampl e</l abel >
    <description>This loads examples. </description>
  </about>
  <upl oad>
    <to>i nput. stri ng(i ndeck)</to>
    <to>i nput. stri ng(datafile)</to>
  </upl oad>
  <download>
    <from>i nput. stri ng(i ndeck)
    <from>i nput. stri ng(datafi l e) </from>
  </download>
  <new>new> xml </new>
  <example>*. xml </example>
  <default>new.xml</default>
</loader>
```



# Assignment #8: Add a loader

## Add a <I oader> to the Rappture interface for your MATLAB script:



Include these examples

Fancy cross  $n_{I} = 13$ 

Flower Palm Branch  $n_1 = 19$   $n_1 = 7$  $n_2 = -7$   $n_2 = -13$   $n_2 = -5$   $n_3 = 3$   $n_3 = 2$